

Numerical Computations of Nanoelectronics Problems

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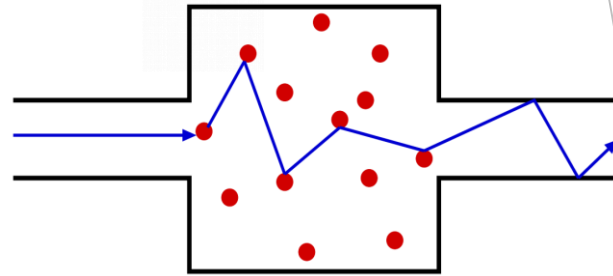
Outline

Three Lectures

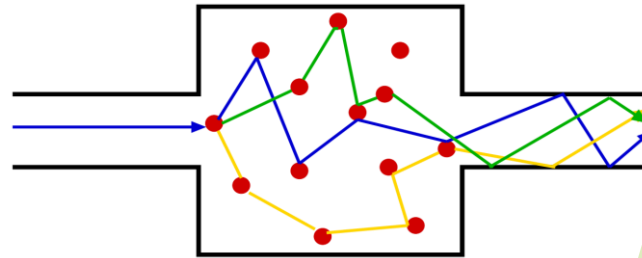
- ▶ Lecture on 5/14
 - ▶ Numerical Calculation of Schrödinger Equation
 - ▶ 1D ∞ Quantum Well
 - ▶ Numerical Newton Iteration
 - ▶ Transcendental Equation (Capacitance of P-N Junction)
 - ▶ Poisson's Equation (Band Diagram of P-N Junction)
- ▶ Lecture on 5/16
 - ▶ Numerical Calculation of Band Structures
 - ▶ 1D atom chain
 - ▶ Graphene Nanoribbon
 - ▶ Graphene
- ▶ Lecture today
 - ▶ Quantum Transport - Non-equilibrium Green's Function

Transport (movement of electrons - current)

- ▶ Semiclassical Transport
 - ▶ Electron as Newtonian pinball



- ▶ Quantum Transport
 - ▶ Electron is in a pure state $|\Psi\rangle$
 - ▶ Recall Wave-particle duality



Transport (current)

- ▶ Semiclassical Transport

- ▶ Macroscopic solid
- ▶ “Boltzman transport equation”

$$J_n = en\mu_n\mathcal{E}_x + eD_n \frac{dn}{dx}$$

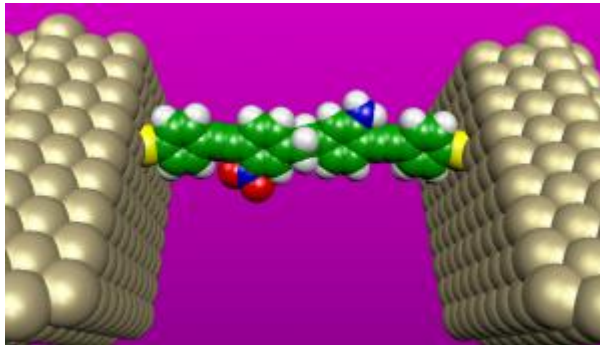
- ▶ Quantum Transport

- ▶ Applied in Nanoscale systems (mesoscopic/microscopic)
- ▶ Where quantum mechanic effects cannot be ignored
- ▶ “Non-equilibrium Green’s Function”

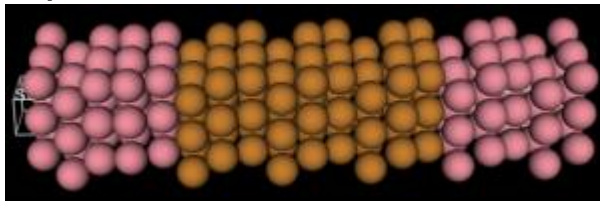
Quantum Transport

► Applications

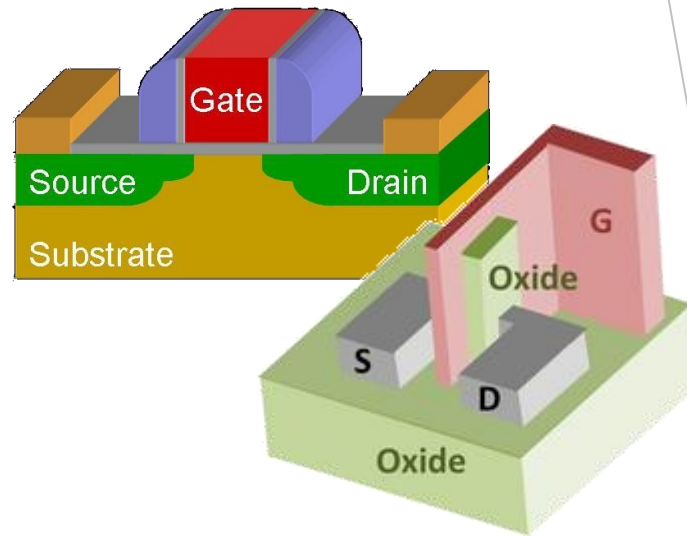
Molecular devices



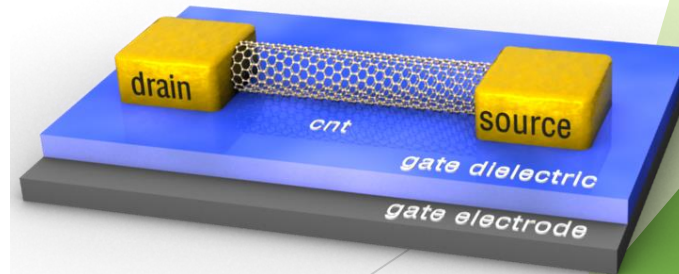
Spin electronic devices



Conventional devices



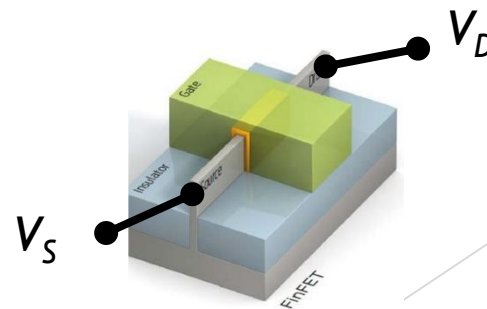
Novel material devices



Quantum Transport

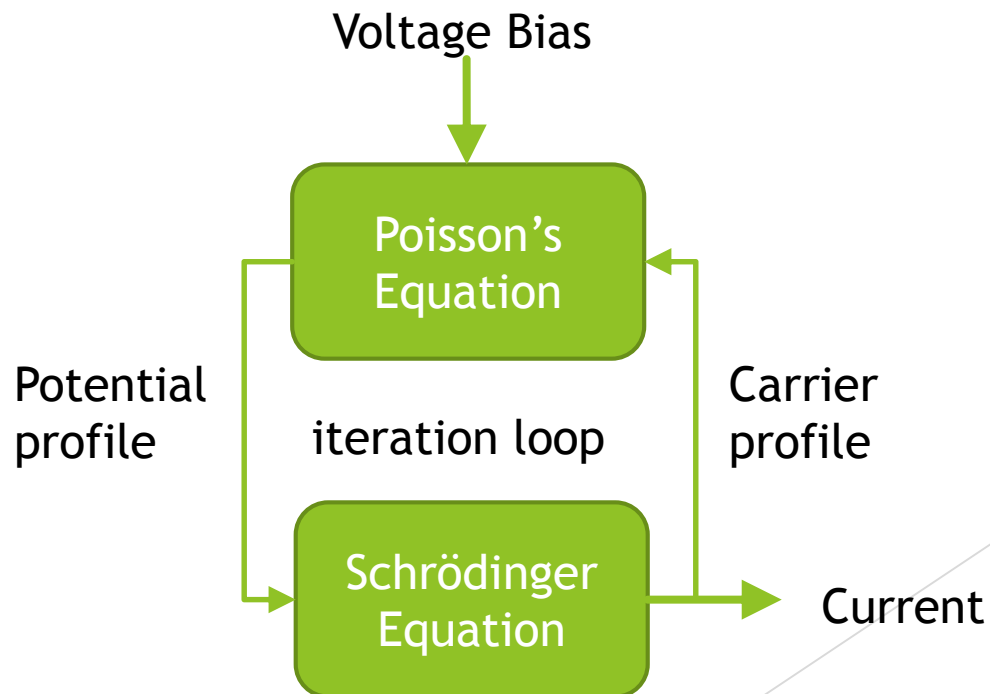
NEGF

- ▶ NEGF
 - ▶ “Non-equilibrium Green’s Function”
 - ▶ A method to solve quantum transport numerically
- ▶ Equilibrium
 - ▶ all chemical potential (Fermi level) gradients are zero
 - ▶ ie. $V_D = V_S$
- ▶ Non-equilibrium



Numerical Quantum Transport

- ▶ Given V_D , V_S , V_G , etc.
- ▶ Solve for I_{DS} , electron profile, potential profile
- ▶ How?



Numerical Quantum Transport

- ▶ Numerical Poisson's Equation

$$\nabla^2 U = Q/\epsilon$$

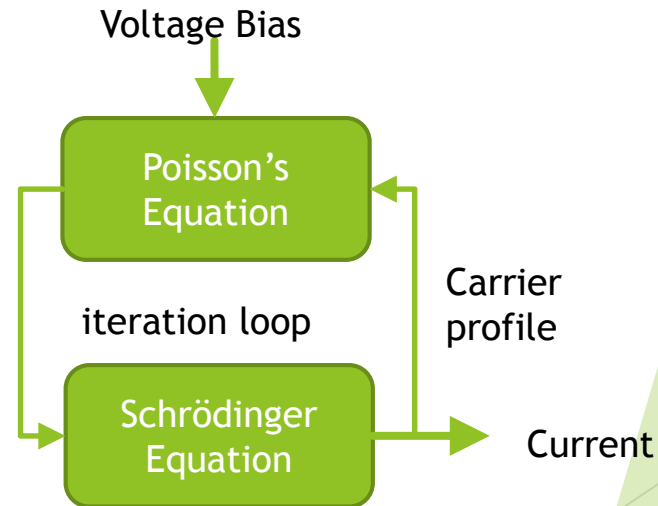
- ▶ Learnt on 5/16
- ▶ Newton Iteration

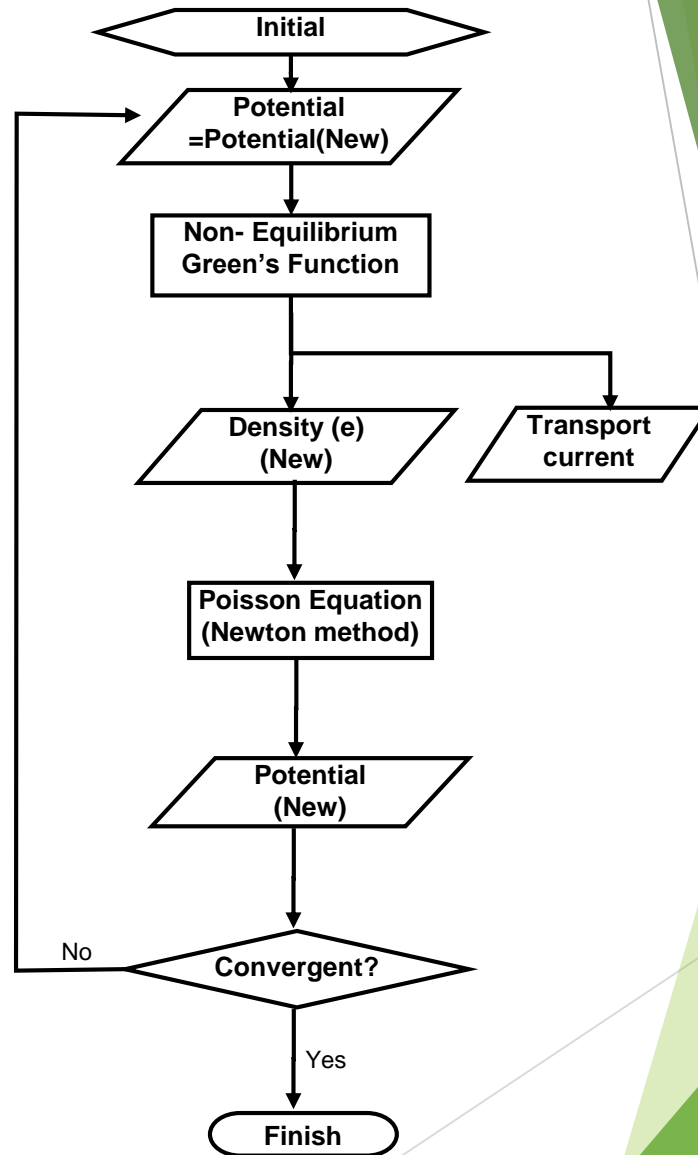
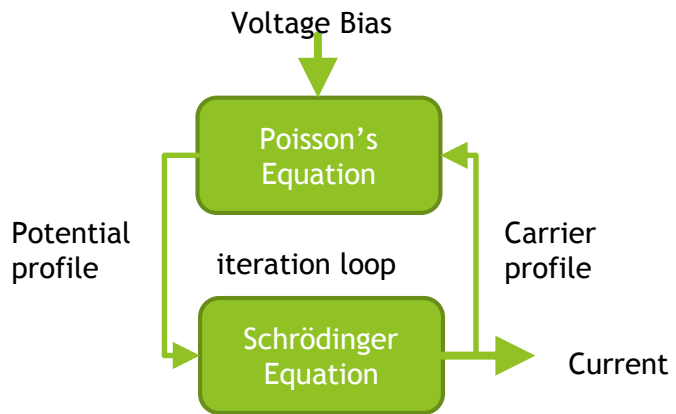
- ▶ Schrodinger Equation

- ▶ Solve using NEGF

So, NEGF is a method to solve Schrodinger Eqn of a non-equilibrium system

Potential profile

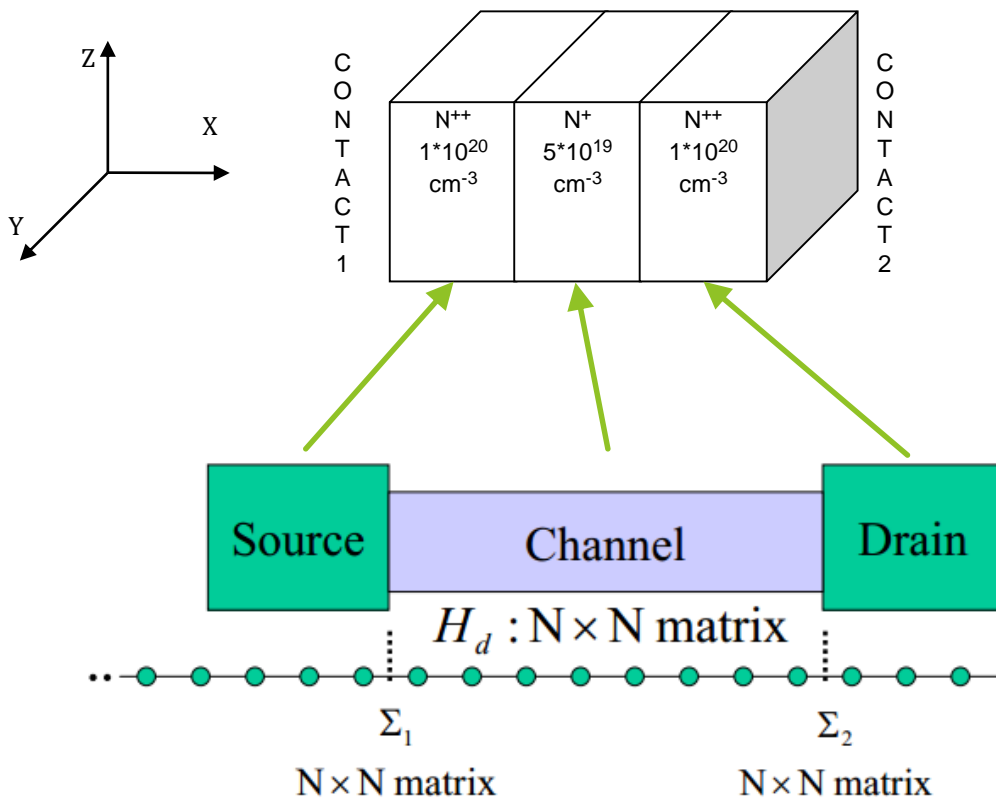




Numerical Quantum Transport

Example 1: 1D silicon resistor

- ▶ 1D device with a large cross-section (effectively infinite in y-z)

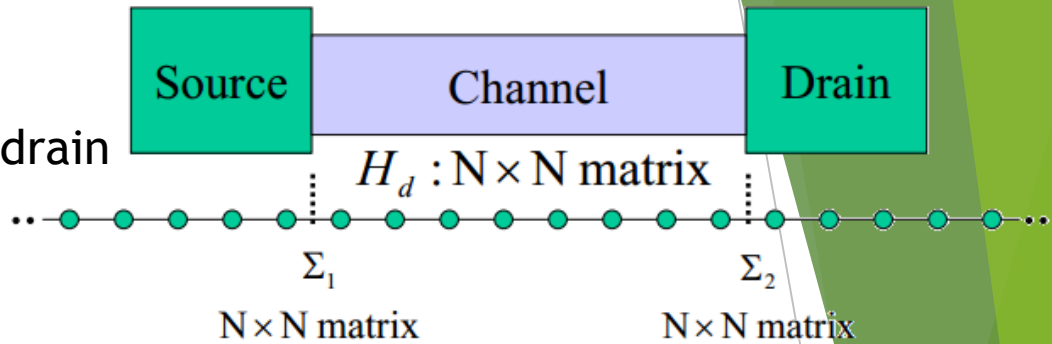


```

L=100;  Ls=15/100*L;
Lc=L-2*Ls;  a=3e-10;
Doping=[ones(Ls,1);...
        1/2*ones(Lc,1);...
        ones(Ls,1)];
Nd0=1e26;
Nd=Nd0*Doping;
    
```

H : Hamiltonian of channel

$\Sigma_{1,2}$: Self energy of source/drain



NEGF Formulism:

$$G(E)_{N \times N} = \left[(E + i0^+)I - H - \Sigma_1(E) - \Sigma_2(E) \right]^{-1} \quad \text{Green's function}$$

$$\Gamma_{1,2}(E)_{N \times N} = i \left[\Sigma_{1,2}(E) - \Sigma_{1,2}(E)^+ \right]$$

$$A_{1,2}(E)_{N \times N} = G(E)\Gamma_{1,2}(E)G(E)^+ \quad \text{spectral function}$$

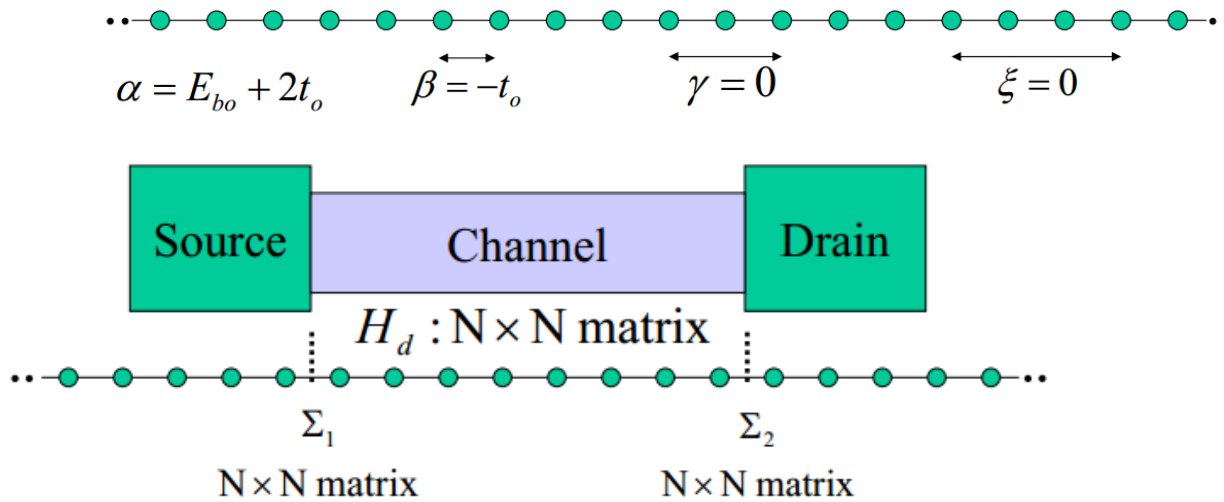
$$A(E)_{N \times N} = A_1(E) + A_2(E) \quad \text{DOS} * 2\pi$$

$$[\rho_k]_{N \times N} = \frac{1}{2\pi} \int_{-\infty}^{+\infty} [f_0(E + E_k - E_{F1})A_1(E) + f_0(E + E_k - E_{F1})A_2(E)] dE$$

$$\begin{aligned} [\rho]_{N \times N} &= \sum_k \frac{1}{2\pi} \int_{-\infty}^{+\infty} [f_0(E + E_k - E_{F1})A_1(E) + f_0(E + E_k - E_{F1})A_2(E)] dE \\ &= \frac{1}{2\pi} \int_{-\infty}^{+\infty} [F_0(E - E_{F1})A_1(E) + F_0(E - E_{F1})A_2(E)] dE \quad \text{Electron density} \end{aligned}$$

$$I = (-q)\text{Trace}([\rho][J_{op}]) \quad \text{current}$$

Recall tight binding model ...



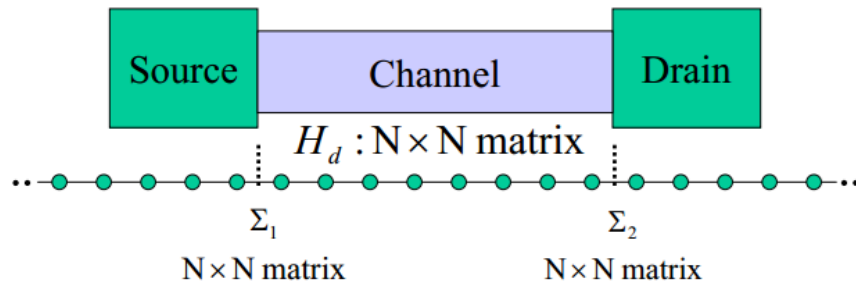
$$H = \begin{bmatrix} 2t_0 + U(x_1) & -t_0 & & & \\ -t_0 & 2t_0 + U(x_2) & \ddots & & \\ & \ddots & \ddots & -t_0 & \\ & & & -t_0 & 2t_0 + U(x_n) \end{bmatrix}$$

where $t_0 = \frac{\hbar^2}{2m_n^*(dx)^2}$

$U(x) = E_c(x)$

(use conduction band as potential energy)

```
h_ = 1.06e-34; q=1.6e-19; m0=9.1e-31;
m=.25*m0; t=h_^2/(2*m*a^2)/q; L=100;
HL= diag(-t*ones(L-1,1), 1) ...
      +diag(2*t*ones(L,1)) ...
      +diag(-t*ones(L-1,1), -1)+diag(U);
```



$$\Sigma_1 = \begin{bmatrix} \frac{-e^{ik_1 dx} \hbar^2}{2m^*(dx)^2} & 0 & \dots \\ 0 & 0 & \ddots \\ \vdots & \ddots & \ddots \end{bmatrix} = \begin{bmatrix} -t \exp(ik_1 dx) & 0 & \dots \\ 0 & 0 & \ddots \\ \vdots & \ddots & \ddots \end{bmatrix}$$

$$\Sigma_2 = \begin{bmatrix} \ddots & \ddots & \vdots \\ \ddots & 0 & 0 \\ \dots & 0 & -t \exp(ik_n dx) \end{bmatrix}$$

$$k_n dx = \arccos\left(1 - \frac{E - U_n}{2t}\right)$$

```
Signal=zeros(L);
k1a=acos(1-(E+i0-U(1))/(2*t));
Signal(1,1)=-t*exp(1i*k1a);
```

```
Sigma2=zeros(L);
kLa=acos(1-(E+i0-U(L))/(2*t));
Sigma2(L,L)=-t*exp(1i*kLa);
```

$$\Gamma_{1,2}(E)_{N \times N} = i[\Sigma_{1,2}(E) - \Sigma_{1,2}(E)^+]$$

```
Gamma1=1i*(Signal-Signal');
Gamma2=1i*(Sigma2-Sigma2');
```

$$G(E)_{N \times N} = \left[(E + i0^+)I - H - \Sigma_1(E) - \Sigma_2(E) \right]^{-1}$$

$$A_{1,2}(E)_{N \times N} = G(E)\Gamma_{1,2}(E)G(E)^+$$

$$A(E)_{N \times N} = A_1(E) + A_2(E)$$

```
G=inv((E+i0)*eye(L)-HL-Sigma1-Sigma2);  
A1=G*Gamma1*G';  
A2=G*Gamma2*G';  
A=A1+A2;
```

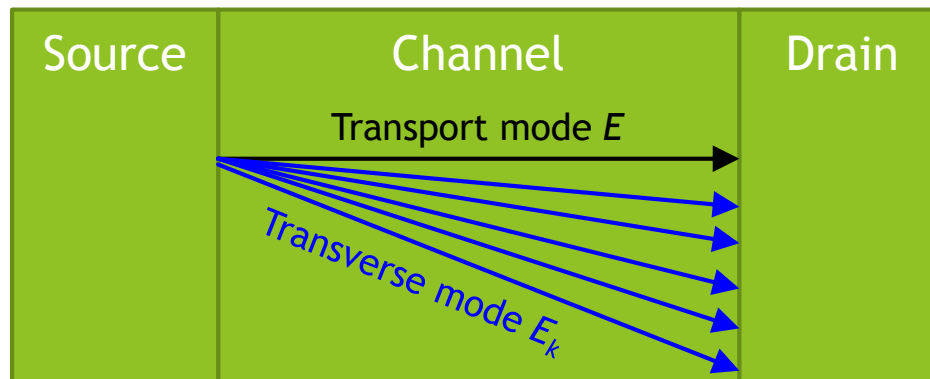
Fermi dirac func Transport energy
 Transverse energy

$$[\rho_k]_{N \times N} = \frac{1}{2\pi} \int_{-\infty}^{+\infty} [f_0(E + E_k - E_{F1})A_1(E) + f_0(E + E_k - E_{F1})A_2(E)] dE$$

$$\begin{aligned} [\rho]_{N \times N} &= \sum_k \frac{1}{2\pi} \int_{-\infty}^{+\infty} [f_0(E + E_k - E_{F1})A_1(E) + f_0(E + E_k - E_{F1})A_2(E)] dE \\ &= \frac{1}{2\pi} \int_{-\infty}^{+\infty} [F_0(E - E_{F1})A_1(E) + F_0(E - E_{F1})A_2(E)] dE \end{aligned}$$

$$f_0(E - \mu) \equiv \left(1 + \frac{1}{v} \exp[(E - \mu)/k_B T] \right)^{-1}$$

$$F_0(E - \mu) = \sum_k f_0(E + \varepsilon_k - \mu) = S \frac{mk_B T}{\pi \hbar^2} \ln \left(1 + \exp \left(\frac{\mu - E}{k_B T} \right) \right)$$



$$F_0(E - \mu) = \sum_k f_0(E + \varepsilon_k - \mu) = S \frac{mk_B T}{\pi \hbar^2} \ln \left(1 + \exp \left(\frac{\mu - E}{k_B T} \right) \right)$$

```
function F=F0(E_miu)
    global m h_ kT S q
    F=S*m*kT*q/(pi*h_^2)*log(1+exp(-(E_miu)/kT));
end
```

$$[\rho]_{N \times N} = \frac{1}{2\pi} \int_{-\infty}^{+\infty} [F_0(E - E_{F1})A_1(E) + F_0(E - E_{F1})A_2(E)] dE = \int_{-\infty}^{+\infty} d\rho$$

$$d\rho = \frac{1}{2\pi} [F_0(E - E_{F1})A_1(E) + F_0(E - E_{F1})A_2(E)]$$

```
drho=1/(2*pi)*(F0(E-miu1)*A1+F0(E-miu2)*A2);
```


$$[\rho]_{N \times N} = \int_{-\infty}^{+\infty} d\rho$$

```
rho=quadv (@ (E) NEGF (E, U, HL, miu1, miu2, Ec0, L),
           E_Min, E_Max, Nd0*a/L);
```

$$d\rho = \frac{1}{2\pi} [F_0(E - E_{F1})A_1(E) + F_0(E - E_{F2})A_2(E)]$$

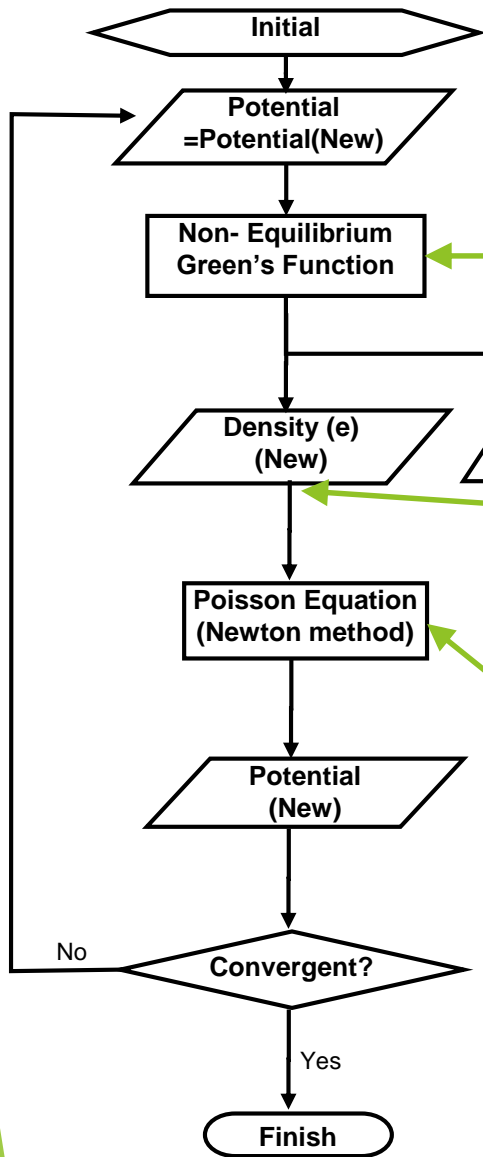
```
function drho=NEGF (E, U, HL, miu1, miu2, Ec0, L)
    global i0
    Sigma1=zeros (L); % Self-energy 1
    k1a=acos (1- (E+i0-Ec0-U(1)) / (2*t));
    Sigma1 (1,1)=-t*exp (1i*k1a);
    Gamma1=1i* (Sigma1-Sigma1');
    Sigma2=zeros (L); % Self-energy 2
    kLa=acos (1- (E+i0-Ec0-U(L)) / (2*t));
    Sigma2 (L,L)=-t*exp (1i*kLa);
    Gamma2=1i* (Sigma2-Sigma2');
    % Green's Function
    G=inv ((E+i0)*eye (L)-HL-Sigma1-Sigma2
    A1=G*Gamma1*G';
    A2=G*Gamma2*G';
    A=A1+A2;
    drho=1/ (2*pi) * (F0 (E-miu1) *A1+F0 (E-miu2) *A2);
end
```

$$[J_{op}] = \frac{\hbar}{2m^* dx^2} \begin{bmatrix} 0 & -i & & \\ i & \ddots & \ddots & \\ & \ddots & \ddots & -i \\ & & i & 0 \end{bmatrix}$$

```
Jop = -(t*q) / (h_*L) *
      (1i*diag(ones(L-1,1), -1)
      + (-1i)*diag(ones(L-1,1), 1));
```

$$I = (-q) \text{Trace}([\rho][J_{op}])$$

```
n_new = (1/a) * real(diag(rho));
I = real((-q) * trace(rho * Jop));
```



```

HL= diag(-t*ones(L-1,1), 1)
      +diag(2*t*ones(L,1))...
      +diag(-t*ones(L-1,1), -1)+diag(U);
rho=quadv(@ (E) NEGF())
function drho=NEGF()

```

```

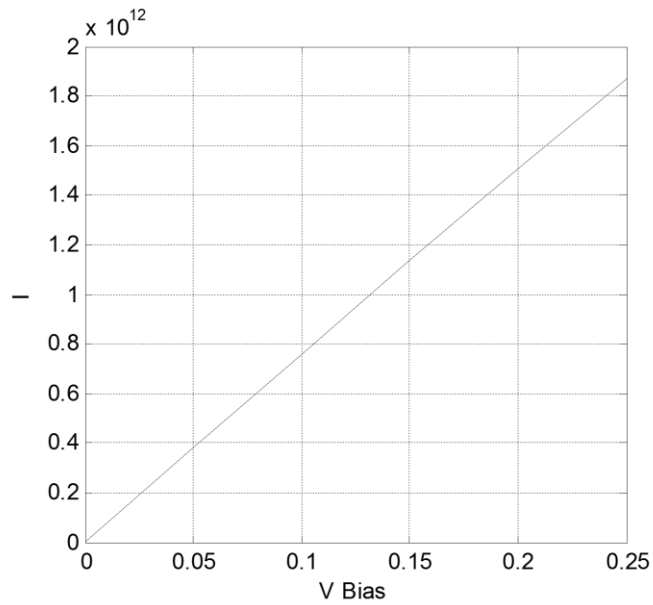
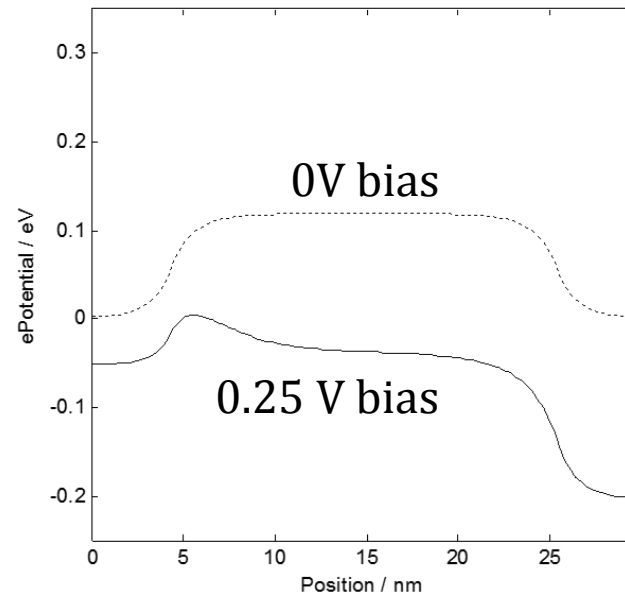
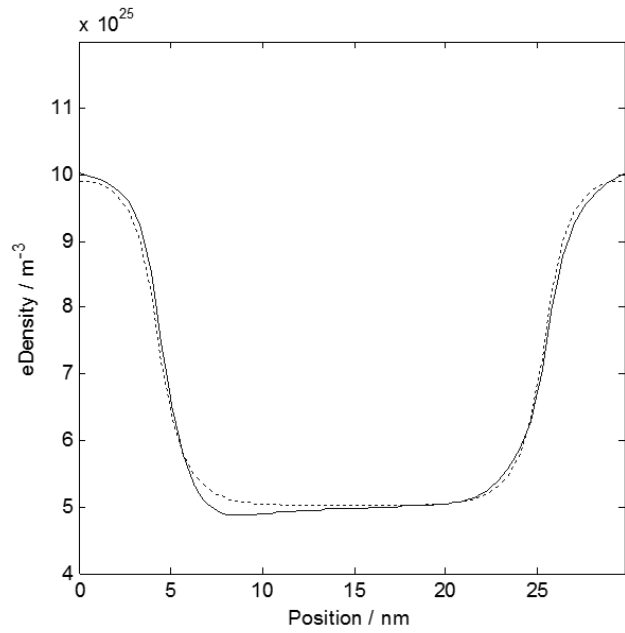
n=(1/a)*real(diag(rho));
I=real((-q)*trace(rho*Jop));

```

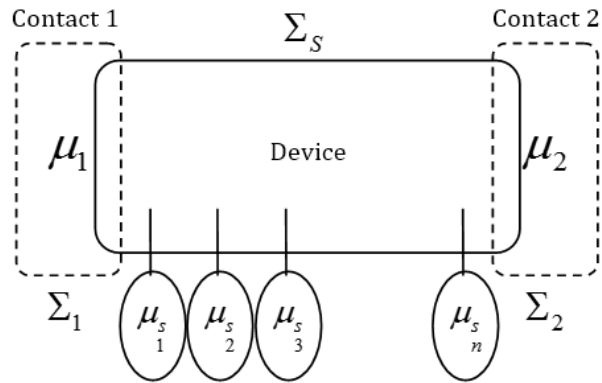
```

while norm(dU)>0.01*norm(U1)
  F_U1=epsilon*d2*U1+q*(n.*exp((U0-U1)/kT)-Nd);
  dF_U1=epsilon*d2+...
           diag((-1/kT)*q*n.*exp((U0-U1)/kT));
  dU=dF_U1\F_U1;
  U2=U1-dU;
  U1=U2;
end

```



Extension - NEGF with Scattering

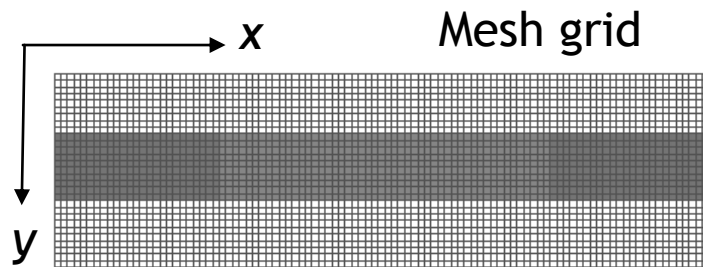
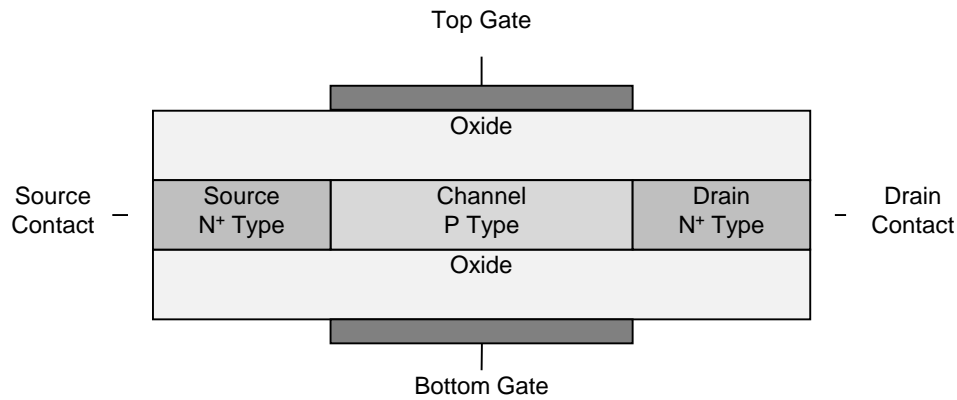


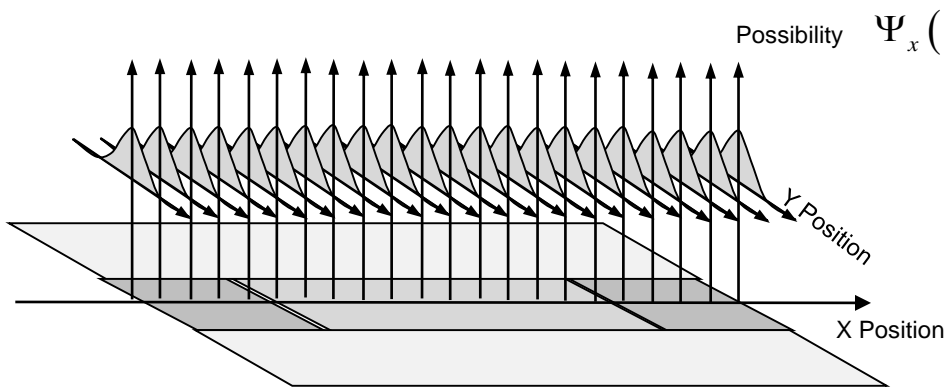
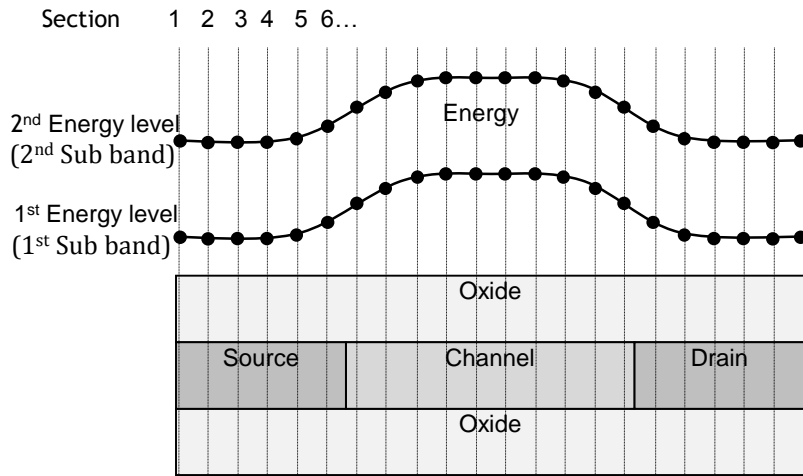
$$G = [EI - H - \Sigma_1 - \Sigma_2 - \Sigma_S]^{-1}$$

$$\Sigma_S = -i \begin{bmatrix} \eta_1 & & & \\ & \eta_2 & & \\ & & \eta_3 & \\ & & & \ddots \end{bmatrix}$$

Numerical Quantum Transport

Example 2: 2D Double gate MOSFET





$$\int_{y_{\min}}^{y_{\max}} \Psi_x(y) dy = 1$$

